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## Thyristor High Voltage, Phase Control SCR, 40 A



PRIMARY CHARACTERISTICS					
I <sub>T(AV)</sub>	35 A				
V <sub>DRM</sub> /V <sub>RRM</sub>	1600 V				
V <sub>TM</sub>	1.45 V				
I <sub>GT</sub>	150 mA				
TJ	-40 °C to +125 °C				
Package	TO-247AD 3L				
Circuit configuration	Single SCR				

#### FEATURES

- $\bullet$  Designed and qualified according to JEDEC  $^{\mbox{\tiny (B)}}$  JESD 47
- Flexible solution for reliable AC power rectification



HALOGEN

- Easy control peak current at charger power up to reduce passive / electromechanical components
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### **APPLICATIONS**

• Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding and battery charge

#### DESCRIPTION

The VS-40TPS16L-M3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. AEC-Q101 qualified P/N available (40TPS16LHM3).

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER	TEST CONDITIONS	VALUES	UNITS				
I <sub>T(AV)</sub>	Sinusoidal waveform	35	А				
I <sub>RMS</sub>		55	A				
V <sub>RRM</sub> /V <sub>DRM</sub>		1600	V				
I <sub>TSM</sub>		500	А				
V <sub>T</sub>	40 A, T <sub>J</sub> = 25 °C	1.45	V				
dv/dt		1000	V/µs				
di/dt		100	A/µs				
TJ		-40 to +125	°C				

VOLTAGE RATINGS								
PART NUMBER	V <sub>RRM</sub> /V <sub>DRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA					
VS-40TPS16L-M3	1600	1700	10					

# VS-40TPS16L-M3



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ABSOLUTE MAXIMUM RATINGS	;				
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average on-state current	I <sub>T(AV)</sub>	$T_{C}$ = 79 °C, 180° conduction half sine wave	)	35	
Maximum continuous RMS on-state current as AC switch	I <sub>T(RMS)</sub>			55	A
Maximum peak, one-cycle	l=a	10 ms sine pulse, rated V <sub>RRM</sub> applied		420	
non-repetitive surge current	ITSM	10 ms sine pulse, no voltage reapplied	1	500	
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	10 ms sine pulse, rated $V_{\text{RRM}}$ applied T <sub>1</sub> = T <sub>1</sub> max.		880	A2-
Maximum 1-t for fusing	1-1	10 ms sine pulse, no voltage reapplied	ıj – ıjınax.	1250	A <sup>2</sup> s
Maximum I²√t for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied		12 500	A²√s
Low level value of threshold voltage	V <sub>T(TO)1</sub>			1.02	V
High level value of threshold voltage	V <sub>T(TO)2</sub>	T 105 %C		1.23	v
Low level value of on-state slope resistance	r <sub>t1</sub>	T <sub>J</sub> = 125 °C		9.74	mΩ
High level value of on-state slope resistance	r <sub>t2</sub>			7.50	1112.2
Maximum pack on state voltage	V	110 A, T <sub>J</sub> = 25 °C	1.92	V	
Maximum peak on-state voltage	V <sub>TM</sub>	90 A, T <sub>J</sub> = 25 °C		1.82	v
Maximum rate of rise of turned-on current	di/dt	T <sub>J</sub> = 25 °C		100	A/µs
Maximum holding current	I <sub>H</sub>	Anode supply = 6 V, resistive load, initial $T_J$	= 1 A, I <sub>T</sub> = 25 °C	300	
Maximum latching current	١L	Anode supply = 6 V, resistive load, $T_J = 25 \degree C$		350	
Maximum university and disease la alexander in the		T <sub>1</sub> = 25 °C		0.5	mA
Maximum reverse and direct leakage current	I <sub>RRM</sub> /I <sub>DRM</sub>	$T_J = 125 \text{ °C}$ $V_R = \text{rated } V_{RRM}/V_{DR}$	$V_{\rm R}$ = rated V <sub>RRM</sub> /V <sub>DRM</sub>		
Maximum rate of rise of off-state voltage	dv/dt	$T_J = T_J$ maximum, linear to 80 % $V_{DRM}$ , $R_g$	k = open	1000	V/µs

TRIGGERING							
PARAMETER	SYMBOL	TEST CO	VALUES	UNITS			
Maximum peak gate power	P <sub>GM</sub>			10	W		
Maximum average gate power	P <sub>G(AV)</sub>			2.5	vv		
Maximum peak gate current	I <sub>GM</sub>			2.5	А		
Maximum peak negative gate voltage	-V <sub>GM</sub>			10	V		
	V <sub>GT</sub>	T <sub>J</sub> = -40 °C	Anode supply = 6 V resistive load	4.0			
Maximum required DC gate voltage to trigger		T <sub>J</sub> = 25 °C		2.5	V		
		T <sub>J</sub> = 125 °C		1.7			
		T <sub>J</sub> = -40 °C		270			
Maximum required DC gate current to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C	Anode supply = 6 V resistive load	150	mA		
		T <sub>J</sub> = 125 °C	Tesistive load	80			
Maximum DC gate voltage not to trigger	V <sub>GD</sub>			0.25	V		
Maximum DC gate current not to trigger	I <sub>GD</sub>	$T_J = 125 \ ^\circ C, V_{DRM} = rated v$	alue	6	mA		

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THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS		UNITS			
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	°C			
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	0.6				
Maximum thermal resistance, junction to ambient	R <sub>thJA</sub>	DC operation	40	°C/W			
Maximum thermal resistance, case to heat sink	R <sub>thCS</sub>	Mounting surface, smooth, and greased	0.25				
Approximate weight			6	g			
			0.21	oz.			
Mounting torqueminimum			6 (5)	kgf · cm			
maximum			12 (10)	(lbf · in)			
Marking device		Case style TO-247AD 3L	40TPS <sup>-</sup>	16L			

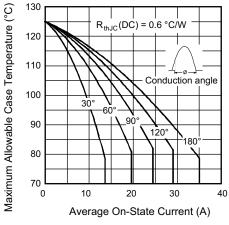


Fig. 1 - Current Rating Characteristics

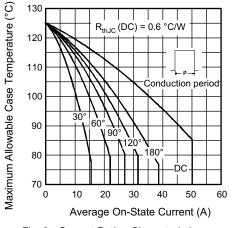


Fig. 2 - Current Rating Characteristics

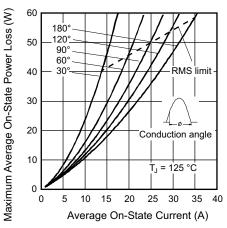


Fig. 3 - On-State Power Loss Characteristics

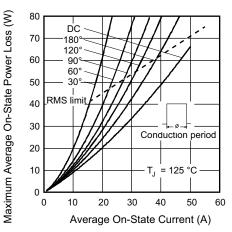
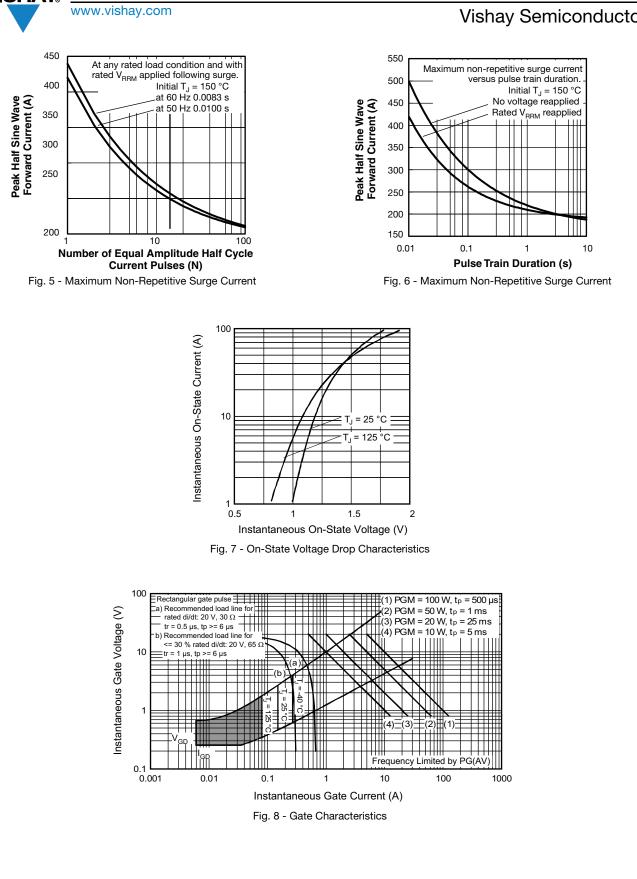


Fig. 4 - On-State Power Loss Characteristics

## **VS-40TPS16L-M3**

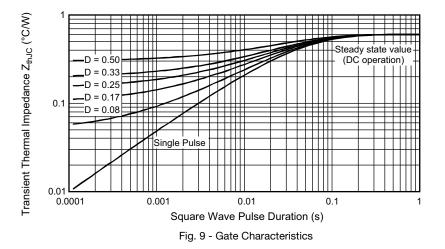
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# VS-40TPS16L-M3

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#### **ORDERING INFORMATION TABLE**

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SHA

Device code	VS-	40	т	Р	S	16	L	-M3	
	1	2	3	4	5	6	7	8	
	1 -	- Visł	nay Sem	niconduc	tors pro	duct			
	2 -	Cur	rent ratii	ng (40 =	40 A)				
	3 -	Circ	uit confi	guratior	1:				
		T =	thyristor	-					
	4 -	Pac	kage:						
		P =	TO-247						
	5 -	Тур	e of silic	on:					
		S =	standar	d recove	ery rectif	ier			
	6 -	Volt	age rati	ngs —				16 = 16	500 V
	7 -	L=	long lea	ds			L		
	8 -	Env	rironmer	ntal digit:					
		M3	= halog	en-free,	RoHS-c	ompliar	nt, and t	erminati	ions lead (F

ORDERING INFORMATION (Example)						
PREFERRED P/N QUANTITY PER TUBE MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION						
VS-40TPS16L-M3	25	500	Antistatic plastic tubes			

LINKS TO RELATED DOCUMENTS					
Dimensions TO-247AD 3L www.vishay.com/doc?95626					
Part marking information TO-247AD 3L www.vishay.com/doc?95007					

 State
 State
 Document Number: 95994

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TO-247AD 3L

#### **DIMENSIONS** in millimeters and inches



View B

SYMBOL	MILLIN	IETERS	INCHES		NOTES
STIVIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.50	2.49	0.059	0.098	
b	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.34	0.065	0.092	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
с	0.38	0.89	0.015	0.035	
c1	0.38	0.84	0.015	0.033	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

(2, 52, 51) (4) Section C - C, D - D, E - E

SYMBOL	MILLIN	IETERS	INC	INCHES	
STNIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.30	0.020	0.051	
E	15.29	15.87	0.602	0.625	3
E1	13.46	-	0.53	-	
е	5.46	BSC	0.215	5 BSC	
ØК	0.2	254	4 0.010		
L	19.81	20.32	0.780	0.800	
L1	3.71	4.29	0.146	0.169	
ØР	3.56	3.66	0.14	0.144	
Ø P1	-	6.98	-	0.275	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	0.178	0.216	
S	5.51 BSC		0.217	' BSC	

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5M-1994

(2) Contour of slot optional

- <sup>(3)</sup> Dimension D and E do not include mold flash. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- <sup>(5)</sup> Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- <sup>(7)</sup> Outline conforms to JEDEC<sup>®</sup> outline TO-247 with exception of dimension A min., D, E min., Q min., S, and note 4

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